This technology is currently not available for licensing

Tech ID: 10088

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- ▶ Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- ▶ Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation
- ▶ High-Quality N-Face GaN, InN, AlN by MOCVD
- ▶ Aluminum-cladding-free Nonpolar III-Nitride LEDs and LDs
- ▶ Low-Cost Zinc Oxide for High-Power-Output, GaN-Based LEDs (UC Case 2010-183)
- ▶ Defect Reduction in GaN films using in-situ SiNx Nanomask
- ▶ Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
- ▶ Low Temperature Deposition of Magnesium Doped Nitride Films
- ▶ Transparent Mirrorless (TML) LEDs
- ▶ Optimization of Laser Bar Orientation for Nonpolar Laser Diodes
- ▶ A Structure For Increasing Mobility In A High-Electron-Mobility Transistor
- ▶ Method for Enhancing Growth of Semipolar Nitride Devices
- ▶ Ultraviolet Laser Diode on Nano-Porous AlGaN template
- ▶ Improved Reliability & Enhanced Performance of III-Nitride Tunnel Junction Optoelectronic Devices
- ▶ Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices
- ▶ Growth of High-Quality, Thick, Non-Polar M-Plane GaN Films
- ▶ Methods for Locally Changing the Electric Field Distribution in Electron Devices
- ▶ High-Efficiency, Mirrorless Non-Polar and Semi-Polar Light Emitting Devices
- ▶ Oxyfluoride Phosphors for Use in White Light LEDs
- ▶ Technique for the Nitride Growth of Semipolar Thin Films, Heterostructures, and Semiconductor Devices
- ▶ (In,Ga,Al)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- ▶ Thermally Stable, Laser-Driven White Lighting Device
- ▶ MOCVD Growth of Planar Non-Polar M-Plane Gallium Nitride
- ▶ GaN-based Vertical Metal Oxide Semiconductor and Junction Field Effect Transistors
- ▶ Methods for Fabricating III-Nitride Tunnel Junction Devices
- ▶ Low-Droop LED Structure on GaN Semi-polar Substrates
- ▶ Contact Architectures for Tunnel Junction Devices
- ▶ Semi-polar LED/LD Devices on Relaxed Template with Misfit Dislocation at Hetero-interface
- ▶ Semipolar-Based Yellow, Green, Blue LEDs with Improved Performance
- ▶ III-Nitride-Based Devices Grown On Thin Template On Thermally Decomposed Material

- Growth of Semipolar III-V Nitride Films with Lower Defect Density

- III-Nitride Tunnel Junction LED with High Wall Plug Efficiency

- Novel Current-Blocking Layer in High-Power Current Aperture Vertical Electron Transistors (CAVETs)

- Iii-N Transistor With Stepped Cap Layers

- Tunable White Light Based on Polarization-Sensitive LEDs

- Cleaved Facet Edge-Emitting Laser Diodes Grown on Semipolar GaN

- Growth of High-Performance M-plane GaN Optical Devices

- Packaging Technique for the Fabrication of Polarized Light Emitting Diodes

- Improved Anisotropic Strain Control in Semipolar Nitride Devices

- III-V Nitride Device Structures on Patterned Substrates

- Method for Increasing GaN Substrate Area in Nitride Devices

- High-Intensity Solid State White Laser Diode

- Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact

- GaN-Based Thermoelectric Device for Micro-Power Generation

- Limiting Strain-Relaxation in III-Nitride Heterostructures by Substrate Patterning

- LED Device Structures with Minimized Light Re-Absorption

- Growth of Planar Semi-Polar Gallium Nitride

- UV Optoelectronic Devices Based on Nonpolar and Semi-polar AlInN and AlInGaN Alloys

- Defect Reduction of Non-Polar and Semi-Polar III-Nitrides

- Enhancing Growth of Semipolar (Al,In,Ga,B)N Films via MOCVD

- III-N Based Material Structures and Circuit Modules Based on Strain Management